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Attorney Docket No.: 5308-413

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Inventor: Saxler et al.

Confirmation No.: 9882

Application No.: 10/849,617

Group Art Unit: 2811

Filed: May 20, 2004

Examiner: Unknown

For: METHODS OF FABRICATING NITRIDE-BASED TRANSISTORS HAVING
REGROWN OHMIC CONTACT REGIONS AND NITRIDE-BASED TRANSISTORS
HAVING REGROWN OHMIC CONTACT REGIONS

Date: August 24, 2004

Mail Stop Amendment
Commissioner for Patents
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INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(b)

Sir:

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It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. § 1.56 and Section 609 of the MPEP.

This Information Disclosure Statement is submitted in accordance with 37 C.F.R. § 1.97(b), within three months of the filing date of the above-referenced application or before the mailing of a first Office Action on the merits, whichever event occurs last. Therefore, no fee is believed due. However, the Commissioner is hereby authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

Respectfully submitted,

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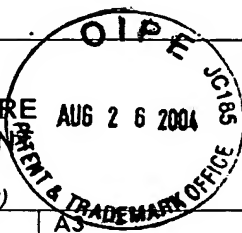
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Erin A. Campion

Substitute form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet **A1** of **A3***Complete if Known*

Application Number	10/849,617
Filing Date	May 20, 2004
First Named Inventor	Saxler
Group Art Unit	2811
Examiner Name	To Be Assigned
Attorney Docket Number	5308-413

U.S. PATENTS AND PATENT PUBLICATIONS

Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		
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	2.	6,639,255		Inoue et al.	10-28-2003
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Examiner Signature

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Substitute form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	10/849,617
				Filing Date	May 20, 2004
				First Named Inventor	Saxler
				Group Art Unit	2811
				Examiner Name	To Be Assigned
Sheet	A2	of	A3	Attorney Docket Number	5308-392

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T
		Office	Number	Kind Code (if known)			
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	45.	JP	2002016087	A	NEC Corp	01-18-2002	Abstract
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	49.	PCT	WO 93/23877	A1	Massachusetts Institute of Technology	11-25-1993	
	50.	EP	0 563 847	A2	Matsushita Electric Industrial Co., Ltd.	10-06-1993	

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Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T	
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Examiner Signature		Date Considered	
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OTHER NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
	72.	Sheppard et al. "High Power Demonstration at 10 GHz with GaN/AlGaIn HEMT Hybrid Amplifiers." Presented at the 58 th DRC, Denver, CO, June 2000.	
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	83.	United States Patent Application entitled "Nitride-Based Transistors with a Protective Layer and a Low-Damage Recess and Methods of Fabrication Thereof," Serial No. 10/758,871, filed January 16, 2004 (Attorney Docket No. 5308-291).	
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	85.	United States Patent Application entitled "Semiconductor Devices Having a Hybrid Channel Layer, Current Aperture Transistors and Methods of Fabricating the Same," Serial No. 10/849,589, filed May 20, 2004 (Attorney Docket No. 5308-412).	
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